

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE6003XM uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. This device is suitable for use as a Battery protection or in other switching application.

General Features

V_{DS} =60V,I_D =3A

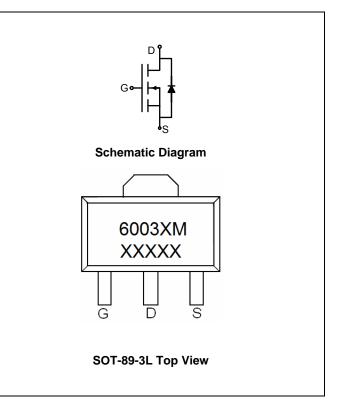
 $R_{DS(ON)}$ <90m Ω @ V_{GS} =10V

 $R_{DS(ON)}$ < 110m Ω @ V_{GS} =4.5V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- Battery switch
- DC/DC converter



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
6003XM	NCE6003XM	SOT-89-3L	Ø180mm	12mm	1000 units

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	3	А
Drain Current-Pulsed (Note 1)	I _{DM}	10	Α
Maximum Power Dissipation	P _D	1.7	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	73.5	°C/W

Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA



http://www.ncepower.com

NCE6003XM

Gate-Body Leakage Current	I_{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.9	1.3	2.0	V
Drain-Source On-State Resistance	В	V _{GS} =10V, I _D =3A	-	68	90	mΩ
Diani-Source On-State Resistance	$R_{DS(ON)}$	V _{GS} =4.5V, I _D =3A	-	80	110	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =3A		3	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ -20\/\/ -0\/	-	270	-	PF
Output Capacitance	Coss	V_{DS} =30V, V_{GS} =0V, F=1.0MHz	-	30	-	PF
Reverse Transfer Capacitance	C _{rss}	r-1.0ivinz	-	21	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	5	-	nS
Turn-on Rise Time	t _r	V_{DD} =30 V , I_{D} =3 A	-	10	-	nS
Turn-Off Delay Time	$t_{d(off)}$ V_{GS} =10V, R_{GEN} =1 Ω		-	12	-	nS
Turn-Off Fall Time	t _f		-	8	-	nS
Total Gate Charge	Qg	\/ -20\/ -24	-	11.5	-	nC
Gate-Source Charge	V _{DS} =30V, I _D =3A,		-	1.8	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	2.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V_{GS} =0 V , I_{S} =3 A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	3	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board, t ≤ 10 sec.
 Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

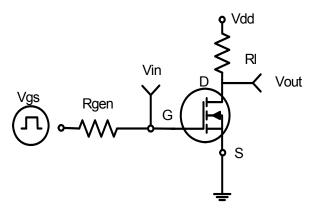
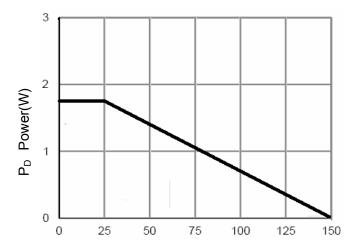


Figure 1:Switching Test Circuit



 T_J -Junction Temperature(°C) Figure 3 Power Dissipation

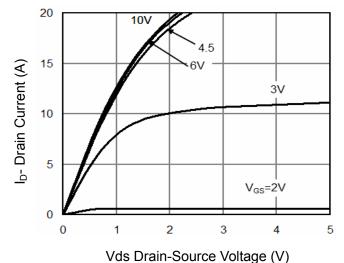


Figure 5 Output Characteristics

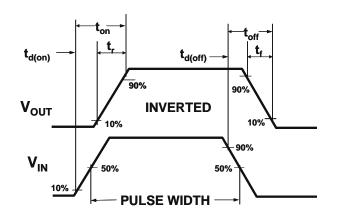
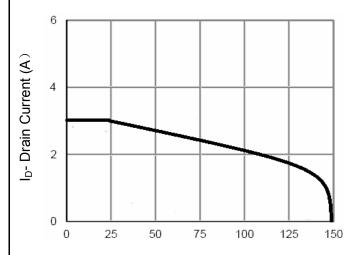


Figure 2:Switching Waveforms



T_J-Junction Temperature(°C)

Figure 4 Drain Current

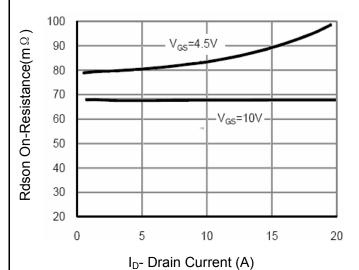


Figure 6 Drain-Source On-Resistance



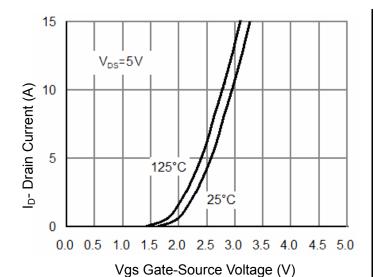
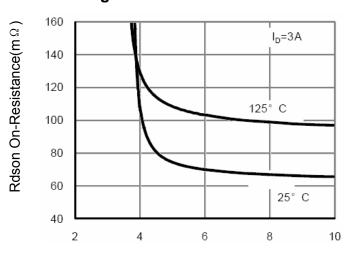


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

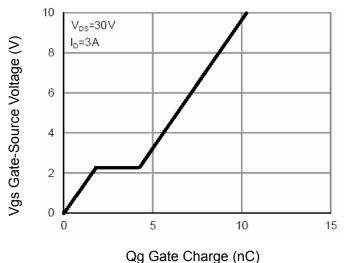


Figure 11 Gate Charge

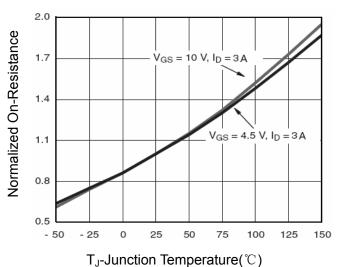
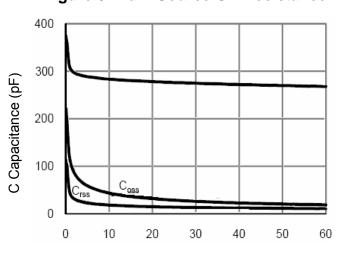


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

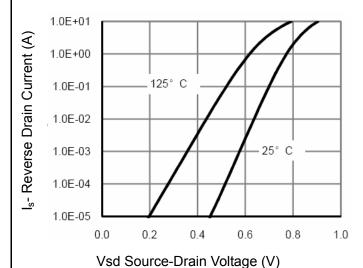
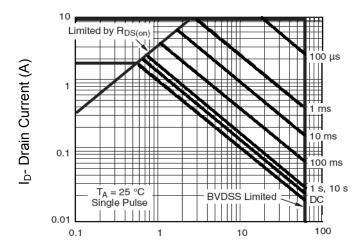


Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

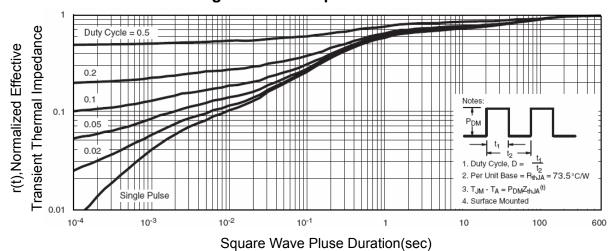
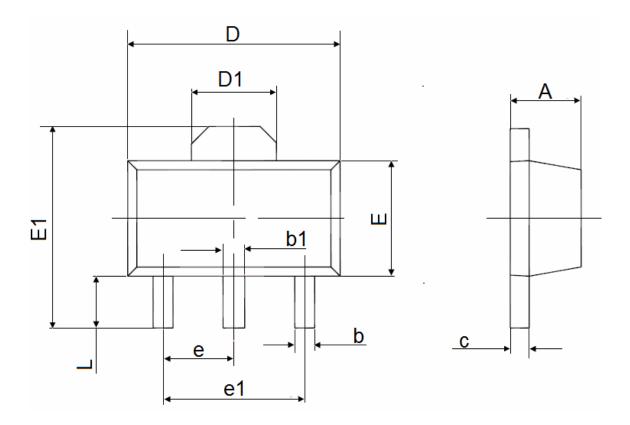


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-89-3L Package Information



Cymbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.400	1.600	0.055	0.063	
b	0.320	0.520	0.013	0.020	
b1	0.400	0.580	0.016	0.023	
С	0.350	0.440	0.014	0.017	
D	4.400	4.600	0.173	0.181	
D1	1.550	REF.	0.061 REF.		
Е	2.300	2.600	0.091	0.102	
E1	3.940	4.250	0.155	0.167	
е	1.500 TYP. 3.000 TYP.		0.060 TYP.		
e1			0.118 TYP.		
L	0.900	1.200	0.035	0.047	

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ± 0.10 mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$

Attention:

- Any and all NCE power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your NCE power representative nearest you before using any NCE power products described or contained herein in such applications.
- NCE power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all NCE power products described or contained herein.
- Specifications of any and all NCE power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- NCE power CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all NCE power products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of NCE power CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. NCE power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the NCE power product that you intend to use.
- This catalog provides information as of Sep.2010. Specifications and information herein are subject to change without notice.